

<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTY DOCKET NO.: ASC-022CPC1</b>  <b>APPLICANT: Wu et al.</b>  <b>SERIAL NO.: 10/603,852</b>  <b>FILING DATE: June 25, 2003</b>  <b>EXAMINER: Owens, Douglas W.</b>  <b>GROUP: 2811</b>			
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U.S. PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
210	A70	2001/0003364	06/14/2001	Sugawara et al.			
	A71	2001/0007789	07/12/2001	Aspar et al.			
	A72	2002/0043660	04/18/2002	Yamazaki et al.			
	A73	2002/0084000	07/04/2002	Fitzgerald			
	A74	2002/0096717	07/25/2002	Chu et al.			
	A75	2002/0100942	08/01/2002	Fitzgerald et al.			
	A76	2002/0123167	09/05/2002	Fitzgerald			
	A77	2002/0123183	09/05/2002	Fitzgerald			
	A78	2002/0125471	09/12/2002	Fitzgerald et al.			
	A79	2002/0168864	11/14/2002	Cheng et al.			
	A80	2003/0003679	01/02/2003	Doyle et al.			
	A81	2003/0013305	01/16/2003	Sugii et al.			
	A82	2003/0034529	02/20/2003	Fitzgerald et al.			
	A83	2003/0057439	03/27/2003	Fitzgerald			
	A84	2003/0102498	06/05/2003	Braithwaite et al.			
	A85	2003/0119280	06/26/2003	Lee et al.			12/02/2002
	A86	2003/0127646	07/10/2003	Christiansen et al.			12/18/2002
	A87	2003/0139000	07/24/2003	Bedell et al.			01/23/2002
	A88	2003/0157787	08/21/2003	Murthy et al.			02/21/2002
	A89	2003/0160300	08/28/2003	Takenaka et al.			02/24/2003
A90	2003/0178681	09/25/2003	Clark et al.			04/02/2003	
A91	2003/0189229	10/09/2003	Mouli			04/05/2002	
A92	2003/0199126	10/23/2003	Chu et al.			04/23/2002	
<b>EXAMINER</b> <i>Douglas W. Owens</i>				<b>DATE CONSIDERED</b> 12/17/04			

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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
DWO	A93	2003/0201458	Clark et al.			05/16/2003	
	A94	2003/0203600	Chu et al.			06/15/2003	
	A95	2003/0207127	Murthy et al.			05/30/2003	
	A96	2003/0215990	Fitzgerald et al.			03/14/2003	
	A97	2003/0218189	Christiansen			11/19/2002	
	A98	2003/0219957	Kuwabara et al.			05/29/2003	
	A99	2003/0227036	Sugiyama et al.			02/21/2003	
	A100	2003/0227057	Lochtefeld et al.			10/04/2002	
	A101	2003/0230778	Park et al.			01/30/2003	
	A102	2003/0232467	Anderson et al.			05/29/2003	
	A103	2004/0005740	Lochtefeld et al.			06/06/2003	
	A104	2004/0007724	Murthy et al.			07/12/2002	
	A105	2004/0009649	Kub et al.			05/20/2003	
	A106	2004/0012037	Venkatesan et al.			07/18/2002	
	A107	2004/0012075	Bedell et al.			07/16/2002	
	A108	2004/0014304	Bhattacharyya			07/18/2002	
	A109	2004/0018699	Boyd et al.			07/24/2002	
	A110	2004/0031979	Lochtefeld			06/06/2003	
	A111	2004/0031990	Jin et al.			08/16/2002	
	A112	2004/0041174	Okihara			03/21/2003	
	A113	2004/0041210	Mouli			09/02/2003	
	A114	2004/0048091	Sato et al.			09/04/2003	
DWO	A115	2004/0048454	Sakaguchi			09/04/2003	
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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
RWO	A116	2004/0051140	03/18/2004	Bhattacharyya		09/12/2002	
	A117	2004/0053477	03/18/2004	Ghyselen et al.		07/09/2003	
	A118	2004/0075149	04/22/2004	Fitzgerald et al.		07/23/2003	
	A119	4,704,302	11/03/1987	Bruel et al.			
	A120	4,710,788	12/01/1987	Dambkes et al.			
	A121	4,987,462	01/22/1991	Kim et al.			
	A122	4,990,979	02/05/1991	Otto			
	A123	4,997,776	03/05/1991	Haramc et al.			
	A124	5,155,571	10/13/1992	Wang et al.			
	A125	5,177,583	01/05/1993	Endo et al.			
	A126	5,240,876	08/34/1993	Gaul et al.			
	A127	5,241,197	08/31/1993	Murakami et al.			
	A128	5,250,445	10/05/1993	Bean et al.			
	A129	5,291,439	03/01/1994	Kauffmann et al.			
	A130	5,298,452	03/29/1994	Meyerson			
	A131	5,316,958	05/31/1994	Meyerson			
	A132	5,399,522	03/21/1995	Ohuri			
	A133	5,424,243	06/13/1995	Takasaki			
	A134	5,426,069	06/20/1995	Selvakumar et al.			
	A135	5,426,316	06/20/1995	Mohammad			
	A136	5,439,843	08/08/1995	Sakaguchi et al.			
	A137	5,461,250	10/24/1995	Burghartz et al.			
RWO	A138	5,479,033	12/26/1995	Baca et al.			
<b>EXAMINER</b> <i>Douglas W. Owens</i>				<b>DATE CONSIDERED</b> <i>12/17/04</i>			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
OK	A139	5,523,243	06/04/1996	Mohammad			
	A140	5,572,043	11/05/1996	Shimizu <i>et al.</i>			
	A141	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
	A142	5,617,351	04/01/1997	Bertin <i>et al.</i>			
	A143	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A144	5,659,187	08/19/1997	Legoues <i>et al.</i>			
	A145	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A146	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A147	5,739,567	04/14/1998	Wong			
	A148	5,777,347	07/07/1998	Bartelink			
	A149	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A150	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A151	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A152	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A153	5,863,830	01/26/1999	Bruel <i>et al.</i>			
	A154	5,882,987	03/16/1999	Srikrishnan			
	A155	5,912,479	06/15/1999	Mori <i>et al.</i>			
	A156	5,963,817	10/05/1999	Chu <i>et al.</i>			
	A157	5,993,677	11/30/1999	Biasse <i>et al.</i>			
	A158	6,013,134	01/11/2000	Chu <i>et al.</i>			
	A159	6,013,563	01/11/2000	Henley <i>et al.</i>			
	A160	6,020,252	02/01/2000	Aspar <i>et al.</i>			
OK	A161	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DKO	A162	6,103,597	08/15/2000	Aspar et al.			
	A163	6,103,599	08/15/2000	Henley et al.			
	A164	6,130,453	10/10/2000	Mei et al.			
	A165	6,133,799	10/17/2000	Favors et al.			
	A166	6,140,687	10/31/2000	Shimomura et al.			
	A167	6,143,636	11/07/2000	Forbes et al.			
	A168	6,160,303	12/12/2000	Fattaruso			
	A169	6,162,705	12/19/2000	Henley et al.			
	A170	6,190,998 B1	02/20/2001	Bruel et al.			
	A171	6,204,529	03/20/2001	Lung et al.			
	A172	6,225,192 B1	05/01/2001	Aspar et al.			
	A173	6,242,324	06/05/2001	Kub et al.			
	A174	6,249,022	06/19/2001	Lin et al.			
	A175	6,251,751 B1	06/26/2001	Chu et al.			
	A176	6,266,278	07/24/2001	Harari et al.			
	A177	6,271,551	08/07/2001	Schmitz et al.			
	A178	6,271,726	08/07/2001	Fransis et al.			
	A179	6,290,804 B1	09/18/2001	Henley et al.			
	A180	6,303,468 B1	10/16/2001	Aspar et al.			
	A181	6,316,301	11/13/2001	Kant			
	A182	6,326,667 B1	12/04/2001	Sugiyama et al.			
	A183	6,329,063	12/11/2001	Lo et al.			
DKO	A184	6,339,232	01/15/2002	Takagi			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DWO	A185	6,344,417 B1	02/05/2002	Usenko			
	A186	6,346,459 B1	02/12/2002	Usenko et al.			
	A187	6,352,909	03/05/2002	Usenko			
	A188	6,355,493 B1	03/12/2002	Usenko			
	A189	6,368,938 B1	04/09/2002	Usenko			
	A190	6,369,438 B1	04/09/2002	Sugiyama et al.			
	A191	6,372,593	04/16/2002	Hattori et al.			
	A192	6,372,609 B1	04/16/2002	Aga et al.			
	A193	6,387,829 B1	05/14/2002	Usenko et al.			
	A194	6,391,740 B1	05/21/2002	Cheung et al.			
	A195	6,399,970	06/04/2002	Kubo et al.			
	A196	6,403,975	06/11/2002	Brunner et al.			
	A197	6,407,406	06/18/2002	Tezuka			
	A198	6,410,371 B1	06/25/2002	Yu et al.			
	A199	6,420,937	07/16/2002	Akatsuka et al.			
	A200	6,425,951	07/30/2002	Chu et al.			
	A201	6,429,061	08/06/2002	Rim			
	A202	6,445,016 B1	09/03/2002	An et al.			
	A203	6,448,152 B1	09/10/2002	Henley et al.			
	A204	6,455,397 B1	09/24/2002	Belford			
	A205	6,458,672 B1	10/01/2002	Henley et al.			
	A206	6,475,072 B1	11/05/2002	Canaperi et al.			
DWO	A207	6,514,836 B2	02/04/2003	Belford			
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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>DWO</i>	A208	6,515,335 B1	02/04/2003	Christiansen <i>et al.</i>			
	A209	6,524,935	02/25/2003	Canaperi <i>et al.</i>			
	A210	6,534,381 B2	03/18/2003	Cheung <i>et al.</i>			
	A211	6,555,839	04/29/2003	Fitzgerald			
	A212	6,583,437 B2	06/24/2003	Mizuno <i>et al.</i>			
	A213	6,593,191	07/15/2003	Fitzgerald			01/17/2001
	A214	6,593,625 B2	07/15/2003	Christiansen <i>et al.</i>			04/03/2002
	A215	6,596,610 B1	07/22/2003	Kuwabara <i>et al.</i>			11/27/2000
	A216	6,602,613	08/05/2003	Fitzgerald			05/16/2000
	A217	6,603,156	08/05/2003	Rim			03/31/2001
	A218	6,607,948 B1	08/19/2003	Sugiyama <i>et al.</i>			08/24/2001
	A219	6,624,047 B1	09/23/2003	Sakaguchi <i>et al.</i>			02/01/2000
	A220	6,624,478 B2	09/23/2003	Anderson <i>et al.</i>			01/30/2002
	A221	6,632,724 B2	10/14/2003	Henley <i>et al.</i>			01/13/2000
	A222	6,635,909 B2	10/21/2003	Clark <i>et al.</i>			03/19/2002
	A223	6,645,831 B1	11/11/2003	Shaheen <i>et al.</i>			05/07/2002
	A224	6,646,322	11/11/2003	Fitzgerald			07/16/2001
	A225	6,649,480	11/18/2003	Fitzgerald <i>et al.</i>			06/19/2001
	A226	6,649,492 B2	11/18/2003	Chu <i>et al.</i>			02/11/2002
	A227	6,656,271 B2	12/02/2003	Yonchara <i>et al.</i>			12/03/1999
	A228	6,664,169 B1	12/16/2003	Iwasaki <i>et al.</i>			06/05/2000
	A229	6,677,183 B2	01/13/2004	Sakaguchi <i>et al.</i>			01/31/2002
<i>DWO</i>	A230	6,677,192	01/13/2004	Fitzgerald			07/16/2001
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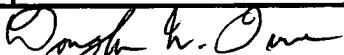
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
OK	A231	6,680,240 B1	01/20/2004	Maszara			06/25/2002		
	A232	6,680,260 B2	01/20/2004	Akiyama <i>et al.</i>			09/17/2002		
	A233	6,690,043 B1	02/10/2004	Usuda <i>et al.</i>			11/22/2000		
	A234	6,703,144	03/09/2004	Fitzgerald			03/18/2003		
	A235	6,703,688	03/09/2004	Fitzgerald			07/16/2001		
	A236	6,706,614 B1	03/16/2004	An <i>et al.</i>			05/15/2002		
	A237	6,706,618 B2	03/16/2004	Takisawa <i>et al.</i>			07/29/2002		
	A238	6,707,106 B1	03/16/2004	Wristers <i>et al.</i>			10/18/2002		
	A239	6,709,903	03/23/2004	Christiansen			04/30/2003		
	A240	6,709,909 B2	03/23/2004	Mizuno <i>et al.</i>			05/19/2003		
	A241	6,713,326	03/30/2004	Cheng <i>et al.</i>			03/04/2003		
	A242	6,723,661	04/20/2004	Fitzgerald			07/16/2001		
	A243	6,730,551	05/04/2004	Lee <i>et al.</i>			08/02/2002		
	A244	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003		
OK	A245	6,750,130	06/15/2004	Fitzgerald			01/07/2001		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OK	B9	41 01 167	07/23/1992	DE				N	Y (Abstract only)
OK	B10	0 514 018	11/19/1992	EP				Y	Y
OK	B11	0 829 908	03/18/1998	EP				N	Y
OK	B12	0 838 858	04/29/1998	EP				N	N
OK	B13	1 020 900	07/19/2000	EP				N	Y
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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
DWJ	B14	1 174 928	01/23/2002	EP				N	Y
DWJ	B15	2 701 599	09/01/1993	FR				Y	Y
DWJ	B16	2 342 777	04/19/2000	GB				Y	Y
DWJ	B17	61/141116	06/28/1986	JP				N	Y (Abstract only)
DWJ	B18	2/210816	08/22/1990	JP				N	Y (Abstract only)
DWJ	B19	3/036717	02/18/1991	JP				N	Y
DWJ	B20	4-307974	10/30/1992	JP				N	N
DWJ	B21	5-166724	07/23/1993	JP				N	Y (Abstract only)
DWJ	B22	6-177046	06/24/1994	JP				N	Y (Abstract only)
DWJ	B23	6-244112	09/02/1994	JP				Y	Y
DWJ	B24	6-252046	09/09/1994	JP				Y	Y
DWJ	B25	7-094420	04/07/1995	JP				N	Y (Abstract only)
DWJ	B26	7-106446	04/21/1995	JP				N	N
DWJ	B27	7-240372	09/12/1995	JP				N	Y (Abstract only)
DWJ	B28	10-270685	10/09/1998	JP				N	Y
DWJ	B29	11-233744	08/27/1999	JP				N	N
DWJ	B30	2000-021783	01/21/2000	JP				N	Y
DWJ	B31	2001-319935	11/16/2001	JP				N	Y
DWJ	B32	2002-076334	03/15/2002	JP				N	Y
DWJ	B33	2002-164520	06/07/2002	JP				N	Y
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<b>U.S. PATENT DOCUMENTS</b>									
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE IF APPROPRIATE</b>		
<b>FOREIGN PATENT DOCUMENTS</b>									
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>COUNTRY CODE</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE</b>	<b>ABSTRACT ONLY</b>	<b>ENGLISH LANG (Y/N)</b>
OKO	B34	2002-289533	10/04/2002	JP				N	Y
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OKO	B36	01/22482	03/29/2001	WO				N	Y
OKO	B37	01/54202	07/26/2001	WO				N	Y
OKO	B38	01/93338	12/06/2001	WO				N	Y
OKO	B39	02/13262	02/14/2002	WO				N	Y
OKO	B40	02/15244	02/21/2002	WO				N	Y
OKO	B41	02/27783	04/04/2002	WO				N	Y
OKO	B42	02/47168	06/13/2002	WO				N	Y
OKO	B43	02/071488	09/12/2002	WO				N	Y
OKO	B44	02/071491	09/12/2002	WO				N	Y
OKO	B45	02/071495	09/12/2002	WO				N	Y
OKO	B46	02/082514	10/17/2002	WO				N	Y
OKO	B47	04/006311	01/15/2004	WO				N	Y
OKO	B48	04/006326	01/15/2004	WO				N	Y
OKO	B49	04/006327	01/15/2004	WO				N	Y
OKO	B50	04/019403	03/04/2004	WO				N	Y
OKO	B51	04/019404	03/04/2004	WO				N	Y
<b>EXAMINER</b> <i>Douglas W. Owens</i>					<b>DATE CONSIDERED</b> <i>12/17/04</i>				

<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTY DOCKET NO.: ASC-022CPC1</b>  <b>APPLICANT: Wu et al.</b>  <b>SERIAL NO.: 10/603,852</b>  <b>FILING DATE: June 25, 2003</b>  <b>EXAMINER: Owens, Douglas W.</b>  <b>GROUP: 2811</b>			
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Dho	C72	Augusto <i>et al.</i> , "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (February 15, 1997), pp. 254-258.					
Dho	C73	Bouillon <i>et al.</i> , "Search for the optimal channel architecture for 0.18/0.12 $\mu$ m bulk CMOS experimental study," IEEE, (1996), pp. 21.2.1-21.2.4.					
Dho	C74	Bufler <i>et al.</i> , "Hole transport in strained Si <sub>1-x</sub> Ge <sub>x</sub> alloys on Si <sub>1-x</sub> Ge <sub>x</sub> substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998), pp. 5597-5602.					
Dho	C75	Burghartz <i>et al.</i> , "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 44, No. 1 (January 1996), pp. 100-104.					
Dho	C76	Canaperi <i>et al.</i> , "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," International Business Machines Corporation, 2002 (abstract).					
Dho	C77	Carlin <i>et al.</i> , "High Efficiency GaAs-on-Si Solar Cells with High Voc Using Graded GeSi Buffers," IEEE (2000), pp. 1006-1011.					
Dho	C78	Cullis <i>et al.</i> , "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," <u>Journal of Vacuum Science and Technology A</u> , Vol. 12, No. 4 (July/August 1994), pp. 1924-1931.					
Dho	C79	Currie <i>et al.</i> , "Carrier mobilities and process stability of strained Si n- and p-MOSFETs on SiGe virtual substrates," <u>Journal of Vacuum Science and Technology B</u> , Vol. 19, No. 6 (Nov/Dec 2001), pp. 2268-2279.					
Dho	C80	Currie <i>et al.</i> , "Controlling Threading Dislocation in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing," <u>Applied Physics Letters</u> , Vol. 72, No. 14 (February 1998), pp. 1718-1720.					
Dho	C81	Eaglesham <i>et al.</i> , "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," <u>Physical Review Letters</u> , Vol. 64, No. 16 (April 16, 1990), pp. 1943-1946.					
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Dk	C83	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electronmobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001), pp. 1232-1250.							
Dk	C84	Fitzgerald <i>et al.</i> , "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering</u> , B67 (1999), pp. 53-61.							
Dk	C85	Garone <i>et al.</i> , "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990), pp. 1275-1277.							
Dk	C86	Godbey <i>et al.</i> , (1990) "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained Si <sub>0.7</sub> Ge <sub>0.3</sub> Layer as an Etch Stop," <u>Journal of the Electrical Society</u> , Vol. 137, No. 10 (October 1990) pp. 3219-3223.							
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Dk	C88	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>0.5</sub> In <sub>0.5</sub> P heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (2002), pp. 4891-4899.							
Dk	C89	Grützmacher <i>et al.</i> , "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993), pp. 2531-2533.							
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Dko	C93	Höck <i>et al.</i> , "Carrier mobilities in modulation doped Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures with respect to FET applications," <u>Thin Solid Films</u> , Vol. 336 (1998), pp. 141-144.						
Dko	C94	Höck <i>et al.</i> , "High hole mobility in Si <sub>0.17</sub> Ge <sub>0.83</sub> channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u> , Vol. 76, No. 26 (June 26, 2000), pp. 3920-3922.						
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Dko	C96	Hsu <i>et al.</i> , "Surface morphology of related Ge <sub>x</sub> Si <sub>1-x</sub> films," <u>Appl. Phys. Lett.</u> , Vol. 61, No. 11 (1992), pp. 1293-1295						
Dko	C97	Huang <i>et al.</i> , "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 7 (July 1998), pp. 1023-1036.						
Dko	C98	Huang <i>et al.</i> , (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", <u>2001 Symposium on VLSI Technology. Digest of Technical Papers</u> , pages 57-58						
Dko	C99	IBM Technical Disclosure Bulletin, "2 Bit/Cell EEPROM Cell Using Band to Band Tunneling for Data Read-Out," Vol. 35, No. 4B (September 1992), pp. 136-140.						
Dko	C100	Ismail <i>et al.</i> , "Modulation-doped n-type Si/SiGe with Inverted Interface," <u>Applied Physics Letters</u> , Vol. 65, No. 10 (September 5, 1994), pp. 1248-1250.						
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OKO	C103	Koester <i>et al.</i> , "Extremely High Transconductance Ge/Si <sub>0.4</sub> Ge <sub>0.6</sub> p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000), pp. 110-112.							
OKO	C104	König <i>et al.</i> , "p-Type Ge-Channel MODFET's with High Transconductance Grown on Si Substrates," <u>IEEE Electron Device Letters</u> , Vol. 14, No. 4 (April 1993), pp. 205-207.							
OKO	C105	König <i>et al.</i> , "SiGe HBTs and HFETs," <u>Solid-State Electronics</u> , Vol. 38, No. 9 (1995), pp. 1595-1602.							
OKO	C106	Kummer <i>et al.</i> , "Low energy plasma enhanced chemical vapor deposition," <u>Materials Science and Engineering B</u> , 89 (2002), pp. 288-295.							
OKO	C107	Kuznetsov <i>et al.</i> , "Technology for high-performance n-channel SiGe modulation-doped field-effect transistors," <u>Journal of Vacuum Science and Technology B</u> , Vol. 13, No. 6 (November/December 1995), pp. 2892-2896.							
OKO	C108	Langdo <i>et al.</i> , (2002) "Preparation of Novel SiGe-free Strained Si on Insulator Substrates" <u>IEEE International SOI Conference</u> , pages 211-212 (XP002263057)							
OKO	C109	Larson, "Integrated Circuit Technology Options for RFIC's - Present Status and Future Directions," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 3 (March 1998), pp. 387-399.							
OKO	C110	Lee <i>et al.</i> , "CMOS RF Integrated Circuits at 5 GHz and Beyond," <u>Proceedings of the IEEE</u> , Vol. 88, No. 10 (October 2000), pp. 1560-1571.							
OKO	C111	Lee <i>et al.</i> , "Strained Ge channel p-type metal-oxide-semiconductor field-effect transistors grown on Si <sub>1-x</sub> Ge <sub>x</sub> /Si virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 20 (November 12, 2001), pp. 3344-3346.							
EXAMINER		Dong L. Q.			DATE CONSIDERED 12/17/04				

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DWO	C112	Lee et al., "Strained Ge channel p-type MOSFETs fabricated on Si <sub>1-x</sub> Ge <sub>x</sub> /Si virtual substrates," <u>Material Research Society Symposium Proceedings</u> , Vol. 686 (2002), pp. A1.9.1-A1.9.5.							
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DWO	C114	Leitz et al., "Hole mobility enhancements in strained Si/Si <sub>1-x</sub> Ge <sub>x</sub> p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si <sub>1-x</sub> Ge <sub>x</sub> (x<y) virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 25 (December 17, 2001), pp. 4246-4248.							
DWO	C115	Li et al., "Design of high speed Si/SiGe heterojunction complementary metal-oxide-semiconductor field effect transistors with reduced short-channel effects," <u>Vacuum Science and Technology A</u> , Vol. 20, No. 3 (May/June 2002), pp. 1030-1033.							
DWO	C116	Lu et al., "High Performance 0.1 μm Gate-Length P-Type SiGe MODFET's and MOS-MODFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 8 (August 2000), pp. 1645-1652.							
DWO	C117	Meyerson et al., "Cooperative Growth Phenomena in Silicon/Germanium Low-Temperature Epitaxy," <u>Applied Physics Letters</u> , Vol. 53, No. 25 (December 19, 1988), pp. 2555-2557.							
DWO	C118	Mizuno et al., "Advanced SOI-MOSFETs with Strained-Si Channel for High Speed CMOS-Electron/Hole Mobility Enhancement," Digest of Technical Papers, 2002 Symposium on VLSI Technology, Honolulu, June 13-15, New York, NY, pp. 210-211.							
DWO	C119	Mizuno et al., "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE IDEM Technical Digest</u> , (1999 International Electron Device Meeting), pp. 934-936.							
DWO	C120	Nayak et al., "High-Mobility Strained-Si PMOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 43, No. 10 (October 1996), pp. 1709-1716.							
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OK	C122	Ota <i>et al.</i> , "Application of heterojunction FET to power amplifier for cellular telephone," <u>Electronic Letters</u> , Vol. 30, No. 11 (May 26, 1994), pp. 906-907.							
OK	C123	Papananos, "Radio-Frequency Microelectronic Circuits for Telecommunication Applications," (1999), pp. 115-117, 188-193.							
OK	C124	Parker <i>et al.</i> , "SiGe Heterostructure CMOS Circuits and Applications," <u>Solid-State Electronics</u> , Vol. 43 (1999), pp. 1497-1506.							
OK	C125	Ransom <i>et al.</i> , "Gate-Self-Aligned n-channel and p-channel Germanium MOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 12 (December 1991), pg. 2695.							
OK	C126	Reinking <i>et al.</i> , "Fabrication of high-mobility Ge p-channel MOSFETs on Si substrates," <u>Electronics Letters</u> , Vol. 35, No. 6 (March 18, 1999), pp. 503-504.							
OK	C127	Rim, "Application of Silicon-Based Heterostructures to Enhanced Mobility Metal-Oxide-Semiconductor Field-Effect Transistors," Ph.D. Thesis, Stanford University, 1999, pp. 1-184.							
OK	C128	Rim <i>et al.</i> , "Enhanced Hole Mobilities in Surface-channel Strained-Si p-MOSFETs," <u>IEEE</u> , (1995), pp. 517-520.							
OK	C129	Rim <i>et al.</i> , "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFETs," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 7 (July 2000), pp. 1406-1415.							
OK	C130	Robbins <i>et al.</i> , "A model for heterogeneous growth of Si <sub>1-x</sub> Ge <sub>x</sub> films for hydrides," <u>Journal of Applied Physics</u> , Vol. 69, No. 6 (March 15, 1991), pp. 3729-3732.							
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Dko	C132	Schäffler, "High-Mobility Si and Ge Structures," <u>Semiconductor Science and Technology</u> , Vol. 12 (1997), pp. 1515-1549.							
Dko	C133	Sugimoto <i>et al.</i> , "A 2V, 500 MHz and 3V, 920 MHz Low-Power Current-Mode 0.6 $\mu$ m CMOS VCO Circuit," <u>Institute of Electronics, Information and Communication Engineers</u> , Vol. E82-C, No. 7 (July 1999), pp. 1327-1329.							
Dko	C134	Ternent <i>et al.</i> , "Metal Gate Strained Silicon MOSFETs for Microwave Integrated Circuits," <u>IEEE</u> (October 2000), pp. 38-43.							
Dko	C135	Tsang <i>et al.</i> , "Measurements of alloy composition and strain in thin $\text{Ge}_x\text{Si}_{1-x}$ layers," <u>Journal of Applied Physics</u> , Vol. 75, No. 12 (June 15, 1994), pp. 8098-8108.							
Dko	C136	Tweet <i>et al.</i> , "Factors determining the composition of strained GeSi layers grown with disilane and germane," <u>Applied Physics Letters</u> , Vol. 65, No. 20 (November 14, 1994), pp. 2579-2581.							
Dko	C137	Welser <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si N-Type Metal-Oxide-Semiconductor Field-Effect Transistors," <u>IEEE Electron Device Letters</u> , Vol. 15, No. 3 (March 1994), pp. 100-102.							
Dko	C138	Welser <i>et al.</i> , "Evidence of Real-Space Hot-Electron Transfer in High Mobility, Strained-Si Multilayer MOSFETs," <u>IEDM</u> , (1993), pp. 545-548.							
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FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
<i>DWO</i>	C142	Xie <i>et al.</i> , "Semiconductor Surface Roughness: Dependence on Sign and Magnitude of Bulk Strain," <u>Physical Review Letters</u> , Vol. 73, No. 22 (November 28, 1994), pp. 3006-3009.							
<i>DWO</i>	C143	Xie <i>et al.</i> , "Very high mobility two-dimensional hole gas in Si/Ge <sub>x</sub> Si <sub>1-x</sub> /Ge structures grown by molecular beam epitaxy," <u>Applied Physics Letters</u> , Vol. 63, No. 16 (October 18, 1993), pp. 2263-2264.							
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EXAMINER <i>Douglas W. Owens</i>				DATE CONSIDERED <i>12/17/04</i>					

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